

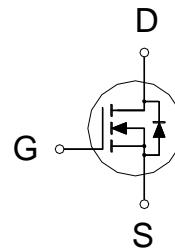
NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK5L4BA**

PDFN 5x6P

Halogen-Free & Lead-Free

PRODUCT SUMMARY

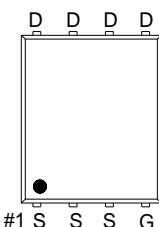
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
30V	3.2mΩ	106A

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.



G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ⁴	$T_C = 25^\circ\text{C}$	I_D	106	A
	$T_C = 100^\circ\text{C}$		67	
Pulsed Drain Current ¹		I_{DM}	200	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	22	
	$T_A = 70^\circ\text{C}$		18	
Avalanche Current		I_{AS}	62	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	192	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	69	W
	$T_C = 100^\circ\text{C}$		27	
Power Dissipation ³	$T_A = 25^\circ\text{C}$	P_D	3.1	W
	$T_A = 70^\circ\text{C}$		2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

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THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		40	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		60	
Junction-to-Case	Steady-State	$R_{\theta JC}$		1.8	

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.⁴Package limitation current is 51A.**ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.5	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
		$V_{DS} = 24V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 8.8A$		3.2	4.8	$m\Omega$
		$V_{GS} = 10V, I_D = 11A$		2.4	3.2	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 11A$		69		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		3905		pF
Output Capacitance	C_{oss}			588		
Reverse Transfer Capacitance	C_{rss}			343		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.1		Ω
Total Gate Charge ²	Q_g	$V_{DS} = 15V, V_{GS} = 10V, I_D = 11A$		73		nC
				35		
Gate-Source Charge ²	Q_{gs}			10		
Gate-Drain Charge ²	Q_{gd}			13		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, I_D \geq 11A, V_{GS} = 10V, R_{GEN} = 6\Omega$		16		nS
Rise Time ²	t_r			42		
Turn-Off Delay Time ²	$t_{d(off)}$			93		
Fall Time ²	t_f			58		

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SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)

Continuous Current ³	I_S				57	A
Forward Voltage ¹	V_{SD}	$I_F = 11\text{A}, V_{GS} = 0\text{V}$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 11\text{A}, dI_F/dt = 100\text{A} / \mu\text{s}$	20			nS
Reverse Recovery Charge	Q_{rr}		11			nC

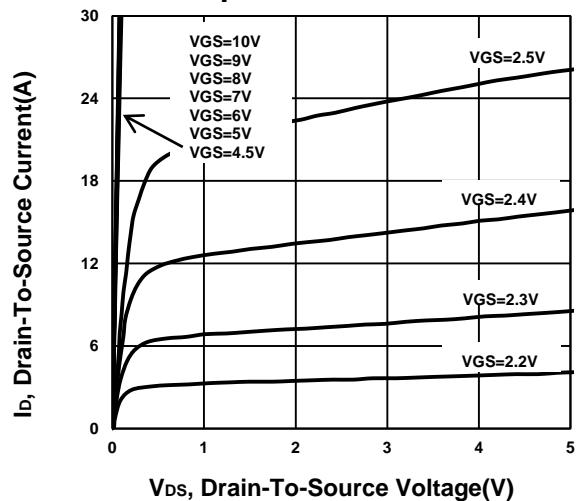
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Package limitation current is 51A.

NIKO-SEM

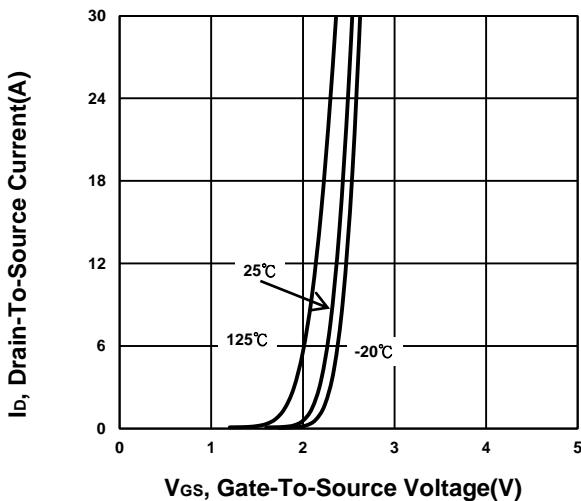
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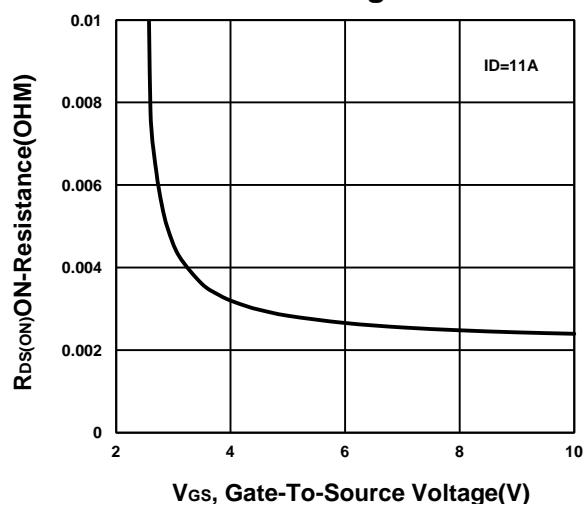
Output Characteristics



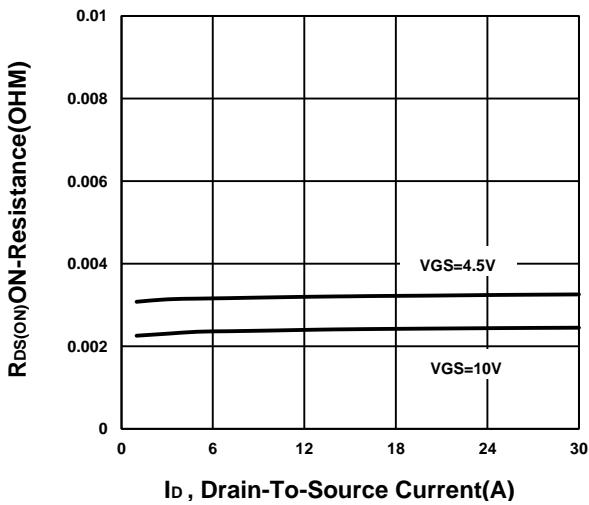
Transfer Characteristics



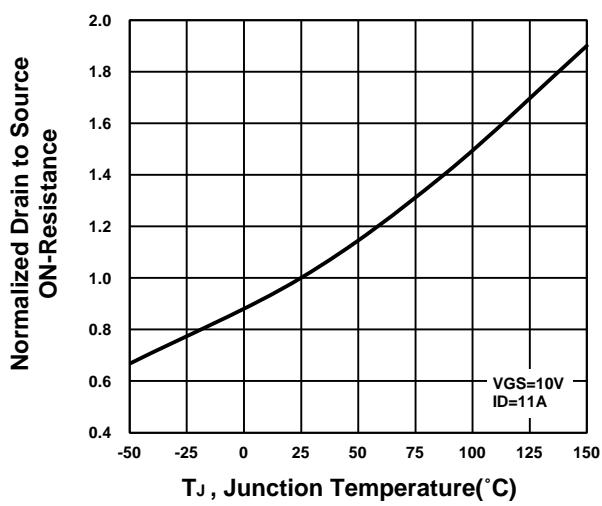
On-Resistance VS Gate-To-Source Voltage



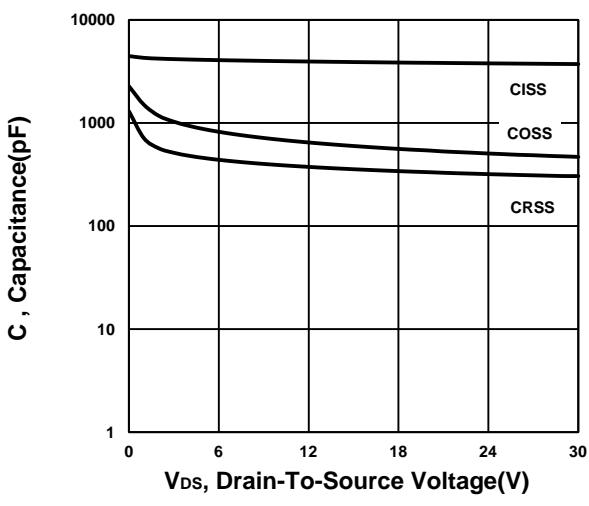
On-Resistance VS Drain Current

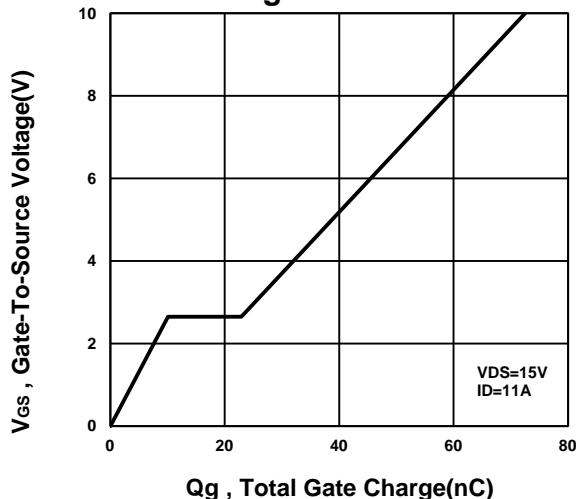
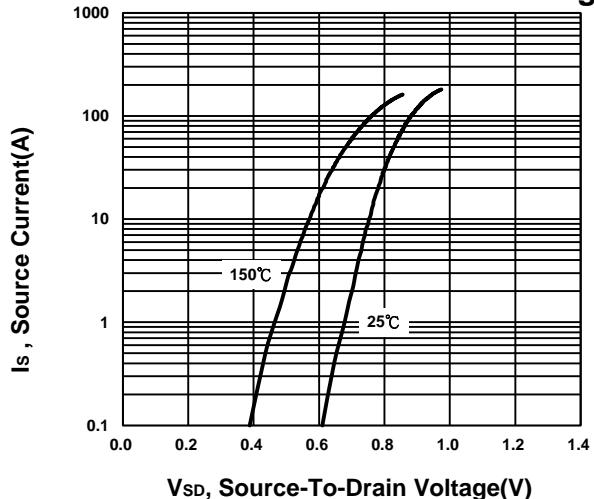
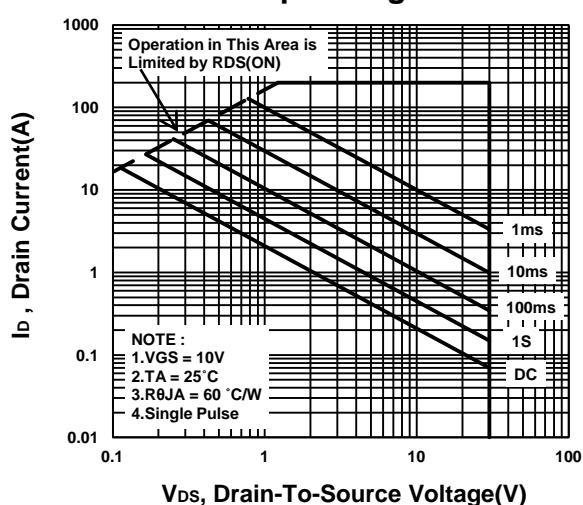
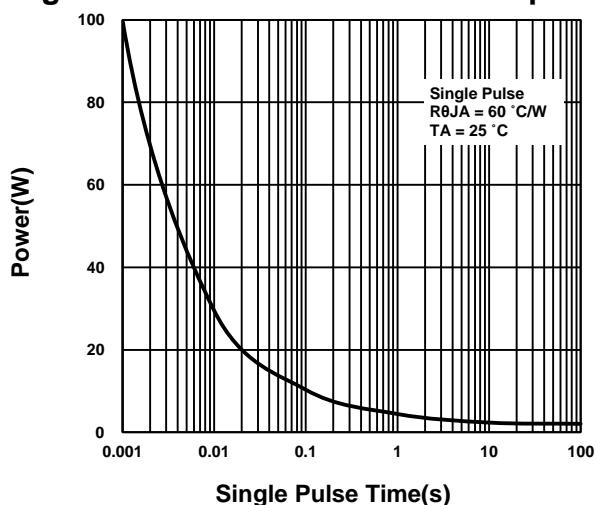
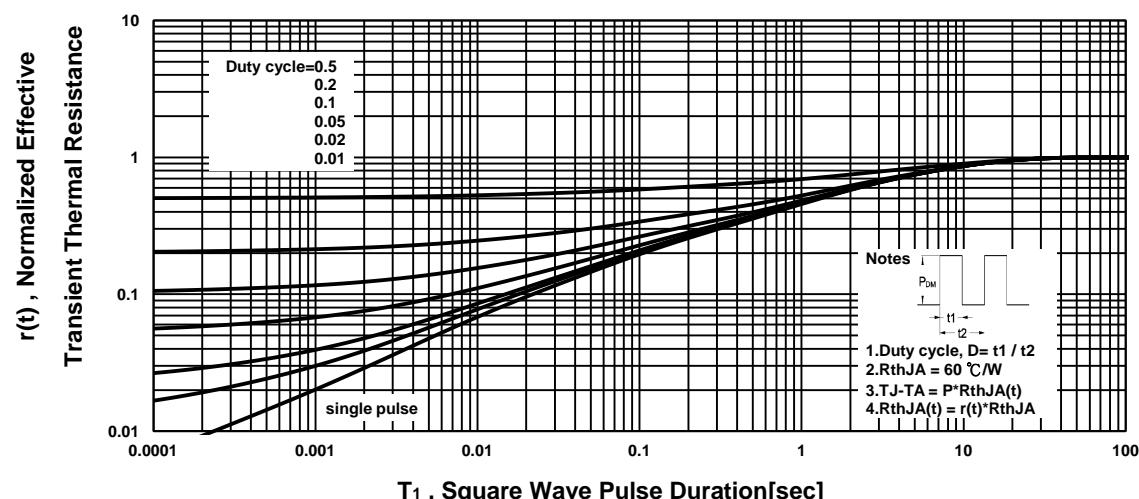


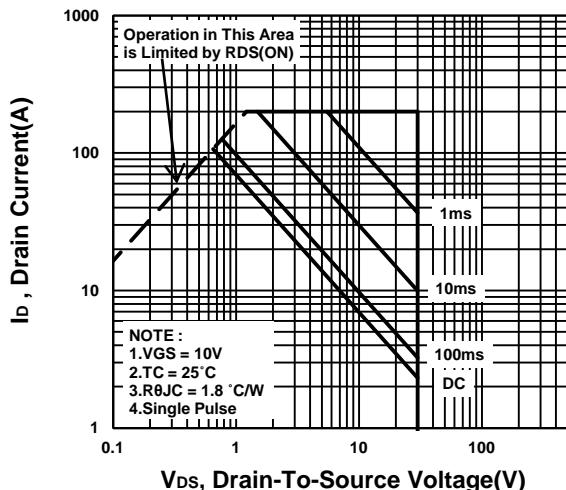
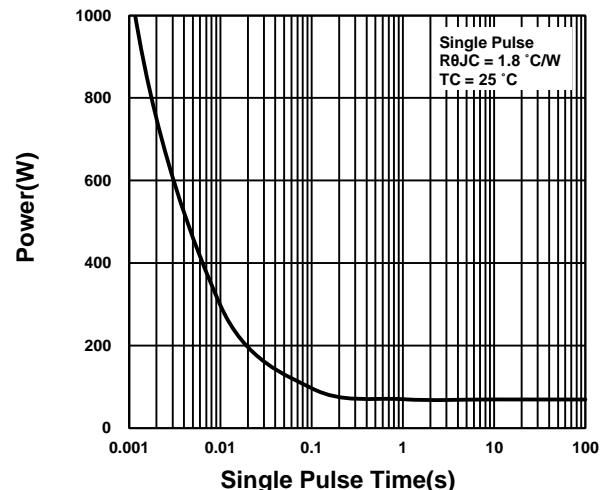
On-Resistance VS Temperature



Capacitance Characteristic



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Halogen-Free & Lead-Free****Gate charge Characteristics****Source-Drain Diode Forward Voltage****Safe Operating Area****Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**

Safe Operating Area**Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**